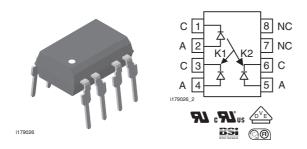




Linear Optocoupler, High Gain Stability, Wide Bandwidth



DESCRIPTION

The IL300 linear optocoupler consists of an AlGaAs IRLED irradiating an isolated feedback and an output PIN photodiode in a bifurcated arrangement. The feedback photodiode captures a percentage of the LEDs flux and generates a control signal (I_{P1}) that can be used to servo the LED drive current. This technique compensates for the LED's non-linear, time, and temperature characteristics. The output PIN photodiode produces an output signal (I_{P2}) that is linearly related to the servo optical flux created by the LED

The time and temperature stability of the input-output coupler gain (K3) is insured by using matched PIN photodiodes that accurately track the output flux of the LED.

FEATURES

- Couples AC and DC signals
- 0.01 % servo linearity
- Wide bandwidth, > 200 kHz
- High gain stability, ± 0.005 %/°C typically
- Low input-output capacitance
- Low power consumption, < 15 mW
- Isolation rated voltage 4420 V_{RMS}
- Internal insulation distance, > 0.4 mm
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



- Power supply feedback voltage / current
- Medical sensor isolation
- · Audio signal interfacing
- Isolated process control transducers
- Digital telephone isolation

AGENCY APPROVALS

- UL file no. E52744
- cUL tested to CSA 22.2 bulletin 5A
- DIN EN 60747-5-5 (VDE 0884-5) available with option 1
- BS
- FIMKO

ORDERING	ORDERING INFORMATION							
	PART NUMBER K3 BIN PACKAGE OPTION TAPE AND REEL Option 7 Option 9							10.16 mm
AGENCY CERTIFIED/ PACKAGE		K3 BIN						
UL, cUL, BSI, FIMKO	0.557 to 1.618	0.765 to 1.181	0.851 to 1.181	0.765 to 0.955	0.851 to 1.061	0.945 to 1.181	0.851 to 0.955	0.945 to 1.061
DIP-8	IL300	IL300-DEFG	-	-	IL300-EF	-	IL300-E	IL300-F
DIP-8, 400 mil, option 6	IL300-X006	IL300-DEFG-X006	-	-	IL300-EF-X006	IL300-FG-X006	IL300-E-X006	IL300-F-X006
SMD-8, option 7	IL300-X007T ⁽¹⁾	IL300-DEFG-X007T ⁽¹⁾	IL300-EFG-X007	IL300-DE-X007T	IL300-EF-X007T ⁽¹⁾	-	IL300-E-X007T	IL300-F-X007
SMD-8, option 9	IL300-X009T ⁽¹⁾	IL300-DEFG-X009T(1)	-	-	IL300-EF-X009T ⁽¹⁾	-	-	IL300-F-X009T ⁽¹⁾
VDE, UL, BSI, FIMKO	0.557 to 1.618	0.765 to 1.181	0.851 to 1.181	0.765 to 0.955	0.851 to 1.061	0.945 to 1.181	0.851 to 0.955	0.945 to 1.061
DIP-8	IL300-X001	IL300-DEFG-X001	-	-	IL300-EF-X001	-	IL300-E-X001	IL300-F-X001
DIP-8, 400 mil, option 6	IL300-X016	IL300-DEFG-X016	-	-	IL300-EF-X016	-	-	IL300-F-X016
SMD-8, option 7	IL300-X017	IL300-DEFG-X017T ⁽¹⁾	-	-	IL300-EF-X017T ⁽¹⁾	-	IL300-E-X017T	IL300-F-X017T ⁽¹⁾
SMD-8, option 9	-	-	-	-	-	-	-	IL300-F-X019T ⁽¹⁾

Note

(1) Also available in tubes, do not put "T" on the end

Rev. 1.9, 31-May-17 1 Document Number: 83622



OPERATION DESCRIPTION

A typical application circuit (Fig. 1) uses an operational amplifier at the circuit input to drive the LED. The feedback photodiode sources current to R1 connected to the inverting input of U1. The photocurrent, I_{P1} , will be of a magnitude to satisfy the relationship of ($I_{P1} = V_{IN}/R1$).

The magnitude of this current is directly proportional to the feedback transfer gain (K1) times the LED drive current ($V_{IN}/R1 = K1 \times I_F$). The op-amp will supply LED current to force sufficient photocurrent to keep the node voltage (Vb) equal to Va.

The output photodiode is connected to a non-inverting voltage follower amplifier. The photodiode load resistor, R2, performs the current to voltage conversion. The output amplifier voltage is the product of the output forward gain (K2) times the LED current and photodiode load, R2 ($V_O = I_F \times K2 \times R2$).

Therefore, the overall transfer gain (V_O/V_{IN}) becomes the ratio of the product of the output forward gain (K2) times the photodiode load resistor (R2) to the product of the feedback transfer gain (K1) times the input resistor (R1). This reduces to

 $V_O/V_{IN} = (K2 \times R2)/(K1 \times R1).$

The overall transfer gain is completely independent of the LED forward current. The IL300 transfer gain (K3) is expressed as the ratio of the output gain (K2) to the feedback gain (K1). This shows that the circuit gain becomes the product of the IL300 transfer gain times the ratio of the output to input resistors

 $V_0/V_{IN} = K3 (R2/R1).$

K1-SERVO GAIN

The ratio of the input photodiode current (I_{P1}) to the LED current (I_{F}) i.e., $K1 = I_{P1}/I_{F}$.

K2-FORWARD GAIN

The ratio of the output photodiode current (I_{P2}) to the LED current (I_F), i.e., $K2 = I_{P2}/I_F$.

K3-TRANSFER GAIN

The transfer gain is the ratio of the forward gain to the servo gain, i.e., K3 = K2/K1.

AK3-TRANSFER FAIN LINEARITY

The percent deviation of the transfer gain, as a function of LED or temperature from a specific transfer gain at a fixed LED current and temperature.

PHOTODIODE

A silicon diode operating as a current source. The output current is proportional to the incident optical flux supplied by the LED emitter. The diode is operated in the photovoltaic or photoconductive mode. In the photovoltaic mode the diode functions as a current source in parallel with a forward biased silicon diode.

The magnitude of the output current and voltage is dependent upon the load resistor and the incident LED optical flux. When operated in the photoconductive mode the diode is connected to a bias supply which reverse biases the silicon diode. The magnitude of the output current is directly proportional to the LED incident optical flux.

LED (LIGHT EMITTING DIODE)

An infrared emitter constructed of AlGaAs that emits at 890 nm operates efficiently with drive current from $500 \,\mu\text{A}$ to 40 mA. Best linearity can be obtained at drive currents between 5 mA to 20 mA. Its output flux typically changes by -0.5 %/°C over the above operational current range.

APPLICATION CIRCUIT

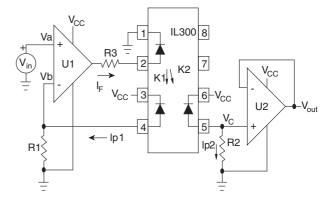


Fig. 1 - Typical Application Circuit



ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
INPUT						
Power dissipation		P _{diss}	160	mW		
Derate linearly from 25 °C			2.13	mW/°C		
Forward current		I _F	60	mA		
Surge current (pulse width < 10 µs)		I _{PK}	250	mA		
Reverse voltage		V _R	5	V		
Thermal resistance		R _{th}	470	K/W		
Junction temperature		Tj	100	°C		
OUTPUT						
Power dissipation		P _{diss}	50	mW		
Derate linearly from 25 °C			0.65	mW/°C		
Reverse voltage		V _R	50	V		
Thermal resistance		R _{th}	1500	K/W		
Junction temperature		Tj	100	°C		
COUPLER						
Total package dissipation at 25 °C		P _{tot}	210	mW		
Derate linearly from 25 °C			2.8	mW/°C		
Storage temperature		T _{stg}	-55 to +150	°C		
Operating temperature		T _{amb}	-55 to +100	°C		

Note

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
maximum ratings for extended periods of the time can adversely affect reliability

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT (LED EMITTER)	120. 00.1201	011111202			1111 0 41	0
Forward voltage	I _F = 10 mA	V _F	-	1.25	1.50	V
V _F temperature coefficient		ΔV _F /Δ°C	-	-2.2	-	mV/°C
Reverse current	V _R = 5 V	I _R	-	1	-	μΑ
Junction capacitance	V _F = 0 V, f = 1 MHz	C _j	-	15	-	pF
Dynamic resistance	I _F = 10 mA	$\Delta V_F/\Delta I_F$	-	6	-	Ω
OUTPUT						
Dark current	V _{det} = -15 V, I _F = 0 A	I _D	-	1	25	nA
Open circuit voltage	I _F = 10 mA	V_D	-	500	-	mV
Short circuit current	I _F = 10 mA	I _{SC}	-	70	-	μΑ
Junction capacitance	V _F = 0 V, f = 1 MHz	Cj	-	12	-	pF
Noise equivalent power	V _{det} = 15 V	NEP	-	4 x 10 ⁻¹⁴	-	W/√Hz
COUPLER						
Input-output capacitance	V _F = 0 V, f = 1 MHz		-	1	-	pF
K1, servo gain (I _{P1} /I _F)	I _F = 10 mA, V _{det} = -15 V	K1	0.006	0.012	0.017	
Servo current (1)(2)	I _F = 10 mA, V _{det} = -15 V	I _{P1}	-	120	-	μΑ
K2, forward gain (I _{P2} /I _F)	I _F = 10 mA, V _{det} = -15 V	K2	0.006	0.012	0.017	
Forward current	I _F = 10 mA, V _{det} = -15 V	I _{P2}	-	120	-	μΑ
K3, transfer gain (K2/K1) (1)(2)	I _F = 10 mA, V _{det} = -15 V	K3	0.56	1	1.65	K2/K1
Transfer gain stability	I _F = 10 mA, V _{det} = -15 V	ΔΚ3/ΔΤ _Α	-	± 0.005	± 0.15	%/°C
Transfer as in linearity	I _F = 1 mA to 10 mA	∆К3	-	± 0.25	-	%
Transfer gain linearity	$I_F = 1$ mA to 10 mA, $T_{amb} = 0$ °C to 75 °C		-	± 0.5	-	%



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ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER TEST CONDITION SYMBOL MIN. TYP. MAX. UNIT						UNIT
PHOTOCONDUCTIVE OPERATION						
Frequency response	I_{Fq} = 10 mA, MOD = ± 4 mA, R_L = 50 Ω	BW (-3 db)	-	200	-	kHz
Phase response at 200 kHz	$V_{det} = -15 \text{ V}$		-	-45	-	Deg.

Notes

 Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements

Bin sorting: K3 (transfer gain) is sorted into bins that are ± 6 %, as follows:
Bin B = 0.620 to 0.696
Bin C = 0.690 to 0.773

Bin A = 0.557 to 0.626 Bin B = 0.620 to 0.696 Bin C = 0.690 to 0.773 Bin D = 0.765 to 0.859 Bin E = 0.851 to 0.955 Bin F = 0.945 to 1.061 Bin G = 1.051 to 1.181 Bin H = 1.169 to 1.311 Bin J = 1.297 to 1.456 Bin J = 1.442 to 1.618

K3 = K2/K1. K3 is tested at $I_F = 10$ mA, $V_{det} = -15$ V

(2) Bin categories: All IL300s are sorted into a K3 bin, indicated by an alpha character that is marked on the part. The bins range from "A" through "J".

The ILX300 is shipped in tubes of 50 each. Each tube contains only one category of K3. The category of the parts in the tube is marked on the tube label as well as on each individual part

(3) Category options: standard IL300 orders will be shipped from the categories that are available at the time of the order. Any of the ten categories may be shipped. For customers requiring a narrower selection of bins, the bins can be grouped together as follows: IL300-DEFG: order this part number to receive categories D, E, F, G only

IL300-EF: order this part number to receive categories E, F only

IL300-E: order this part number to receive category E only

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Switching time	$\Delta I_F = 2$ mA, $I_{Fq} = 10$ mA	t _r	1	1	-	μs
Switching time		t _f	-	1	-	μs
Rise time		t _r	-	1.75	-	μs
Fall time		t _f	1	1.75	-	μs

COMMON MODE TRANSIENT IMMUNITY						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Common mode capacitance	$V_F = 0 V, f = 1 MHz$	C _{CM}	-	0.5	-	pF
Common mode rejection ratio	$f = 60 \text{ Hz}, R_L = 2.2 \text{ k}\Omega$	CMRR	-	130	-	dB

SAFETY AND INSULATION RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
Climatic classification	According to IEC 68 part 1		55 / 100 / 21			
Comparative tracking index		CTI	175			
Maximum rated withstanding isolation voltage	t = 1 min	V _{ISO}	4420	V _{RMS}		
Maximum transient isolation voltage		V _{IOTM}	10 000	V _{peak}		
Maximum repetitive peak isolation voltage		V _{IORM}	890	V _{peak}		
Isolation resistance	$V_{IO} = 500 \text{ V}, T_{amb} = 25 ^{\circ}\text{C}$	R _{IO}	≥ 10 ¹²	Ω		
isolation resistance	V_{IO} = 500 V, T_{amb} = 100 °C	R _{IO}	≥ 10 ¹¹	Ω		
Output safety power		P _{SO}	400	mW		
Input safety current		I _{SI}	275	mA		
Safety temperature		T _S	175	°C		
Creepage distance			≥ 7	mm		
Clearance distance			≥ 7	mm		
Insulation thickness		DTI	≥ 0.4	mm		

Note

• As per IEC 60747-5-5, § 7.4.3.8.2, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits





TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

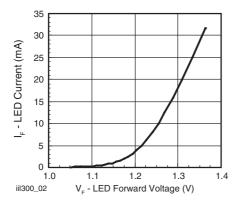


Fig. 2 - LED Forward Current vs. Forward Voltage

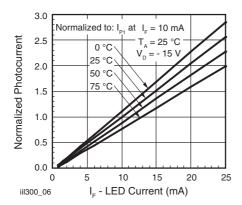


Fig. 3 - Normalized Servo Photocurrent vs. LED Current and Temperature

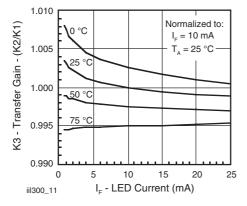


Fig. 4 - Normalized Transfer Gain vs. LED Current and Temperature

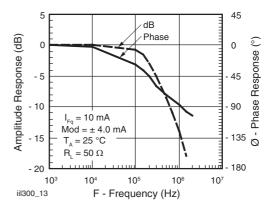


Fig. 5 - Amplitude and Phase Response vs. Frequency

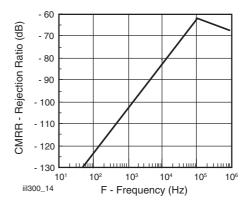


Fig. 6 - Common-Mode Rejection

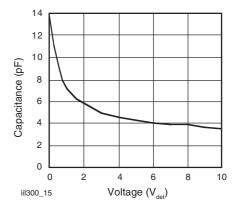


Fig. 7 - Photodiode Junction Capacitance vs. Reverse Voltage



APPLICATION CONSIDERATIONS

In applications such as monitoring the output voltage from a line powered switch mode power supply, measuring bioelectric signals, interfacing to industrial transducers, or making floating current measurements, a galvanically isolated, DC coupled interface is often essential. The IL300 can be used to construct an amplifier that will meet these needs.

The IL300 eliminates the problems of gain nonlinearity and drift induced by time and temperature, by monitoring LED output flux.

A pin photodiode on the input side is optically coupled to the LED and produces a current directly proportional to flux falling on it. This photocurrent, when coupled to an amplifier, provides the servo signal that controls the LED drive current.

The LED flux is also coupled to an output PIN photodiode. The output photodiode current can be directly or amplified to satisfy the needs of succeeding circuits.

ISOLATED FEEDBACK AMPLIFIER

The IL300 was designed to be the central element of DC coupled isolation amplifiers. Designing the IL300 into an amplifier that provides a feedback control signal for a line powered switch mode power is quite simple, as the following example will illustrate.

See Fig. 12 for the basic structure of the switch mode supply using the Infineon TDA4918 push-pull switched power supply control cChip. Line isolation are provided by the high frequency transformer. The voltage monitor isolation will be provided by the IL300.

The isolated amplifier provides the PWM control signal which is derived from the output supply voltage. Fig. 13 more closely shows the basic function of the amplifier.

The control amplifier consists of a voltage divider and a non-inverting unity gain stage. The TDA4918 data sheet indicates that an input to the control amplifier is a high quality operational amplifier that typically requires a + 3 V signal. Given this information, the amplifier circuit topology shown in Fig. 14 is selected.

The power supply voltage is scaled by R1 and R2 so that there is + 3 V at the non-inverting input (V_a) of U1. This voltage is offset by the voltage developed by photocurrent flowing through R3. This photocurrent is developed by the optical flux created by current flowing through the LED. Thus as the scaled monitor voltage (V_a) varies it will cause a change in the LED current necessary to satisfy the differential voltage needed across R3 at the inverting input. The first step in the design procedure is to select the value of R3 given the LED quiescent current (I_{Fq}) and the servo gain (K1). For this design, I_{Fq} = 12 mA. Fig. 4 shows the servo photocurrent at I_{Fq} is found to be 100 mA. With this data R3 can be calculated.

$$R3 = \frac{V_b}{I_{Pl}} = \frac{3 \text{ V}}{100 \, \mu A} = 30 \text{ k}\Omega$$

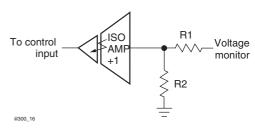


Fig. 8 - Isolated Control Amplifier

For best input offset compensation at U1, R2 will equal R3. The value of R1 can easily be calculated from the following.

$$R1 = R2 \times \left(\frac{V_{MONITOR}}{V_{a}} - 1 \right)$$

The value of R5 depends upon the IL300 Transfer Gain (K3). K3 is targeted to be a unit gain device, however to minimize the part to part Transfer Gain variation, Infineon offers K3 graded into \pm 5 % bins. R5 can determined using the following equation,

$$R5 = \frac{V_{OUT}}{V_{MONITOR}} \times \frac{R3 \times (R1 + R2)}{R2 \times K3}$$

or if a unity gain amplifier is being designed $(V_{MONITOR} = V_{OUT}, R1 = 0)$, the equation simplifies to:

$$R5 = \frac{R3}{K3}$$

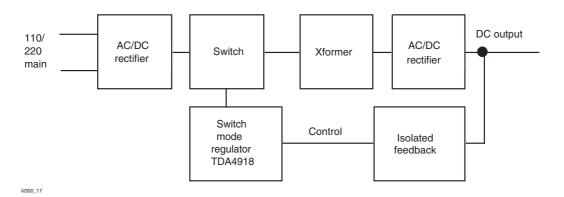


Fig. 9 - Switching Mode Power Supply

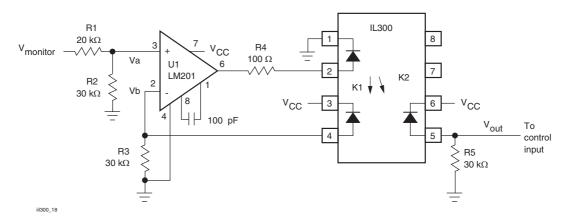


Fig. 10 - DC Coupled Power Supply Feedback Amplifier





Table 1. Gives the value of R5 given the production K3 bin.

TABLE 1 - R5 SELECTION							
BIN		К3		R5 RESISTOR			
DIN	MIN.	MAX.	TYP.	1 % kΩ			
A	0.560	0.623	0.59	51.1			
В	0.623	0.693	0.66	45.3			
С	0.693	0.769	0.73	41.2			
D	0.769	0.855	0.81	37.4			
E	0.855	0.950	0.93	32.4			
F	0.950	1.056	1	30			
G	1.056	1.175	1.11	27			
Н	1.175	1.304	1.24	24			
I	1.304	1.449	1.37	22			
J	1.449	1.610	1.53	19.4			

The last step in the design is selecting the LED current limiting resistor (R4). The output of the operational amplifier is targeted to be 50 % of the $V_{\rm CC}$, or 2.5 V. With an LED quiescent current of 12 mA the typical LED (V_F) is 1.3 V. Given this and the operational output voltage, R4 can be calculated.

$$R4 = \frac{V_{opamp} - V_F}{I_{Fq}} = \frac{2.5 \text{ V} - 1.3 \text{ V}}{12 \text{ mA}} = 100 \Omega$$

The circuit was constructed with an LM201 differential operational amplifier using the resistors selected. The amplifier was compensated with a 100 pF capacitor connected between pins 1 and 8.

The DC transfer characteristics are shown in Fig. 17. The amplifier was designed to have a gain of 0.6 and was measured to be 0.6036. Greater accuracy can be achieved by adding a balancing circuit, and potentiometer in the input divider, or at R5. The circuit shows exceptionally good gain linearity with an RMS error of only 0.0133 % over the input voltage range of 4 V to 6 V in a servo mode; see Fig. 15.

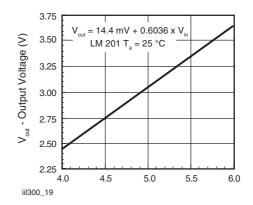


Fig. 11 - Transfer Gain

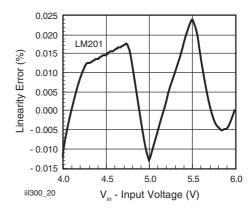


Fig. 12 - Linearity Error vs. Input Voltage

The AC characteristics are also quite impressive offering a -3 dB bandwidth of 100 kHz, with a -45 $^{\circ}$ phase shift at 80 kHz as shown in Fig. 16.



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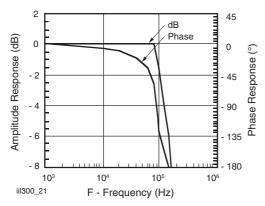


Fig. 13 - Amplitude and Phase Power Supply Control

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The same procedure can be used to design isolation amplifiers that accept bipolar signals referenced to ground. These amplifiers circuit configurations are shown in Fig. 17. In order for the amplifier to respond to a signal that swings above and below ground, the LED must be pre biased from a separate source by using a voltage reference source (V_{ref1}). In these designs, R3 can be determined by the following equation.

$$R3 = \frac{V_{ref1}}{I_{P1}} = \frac{V_{ref1}}{K1I_{Fq}}$$

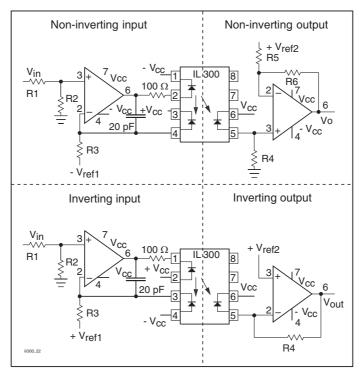


Fig. 14 - Non-inverting and Inverting Amplifiers

TABLE 2 - OPTOLINEAR AMPLIEFIERS						
AMPLIFIER	INPUT	OUTPUT	GAIN	OFFSET		
Non-inverting	Inverting	Inverting	$\frac{V_{OUT}}{V_{IN}} = \frac{K3 \times R4 \times R2}{R3 \times (R1 \times R2)}$	$V_{ref2} = \frac{V_{ref1} \times R4 \times K3}{R3}$		
Non-inverting	Non-inverting	Non-inverting	$\frac{V_{OUT}}{V_{IN}} = \frac{K3 \times R4 \times R2 \times (R5 + R6)}{R3 \times R5 \times (R1 \times R2)}$	$V_{ref2} = \frac{-V_{ref1} \times R4 \times (R5 + R6) \times K3}{R3 \times R6}$		
Inverting	Inverting	Non-inverting	$\frac{V_{OUT}}{V_{IN}} = \frac{- K3 \times R4 \times R2 \times (R5 + R6)}{R3 \times (R1 \times R2)}$	$V_{ref2} = \frac{V_{ref1} \times R4 \times (R5 + R6) \times K3}{R3 \times R6}$		
inverting	Non-inverting	Inverting	$\frac{V_{OUT}}{V_{IN}} = \frac{-K3 \times R4 \times R2}{R3 \times (R1 \times R2)}$	$V_{ref2} = \frac{-V_{ref1} \times R4 \times K3}{R3}$		



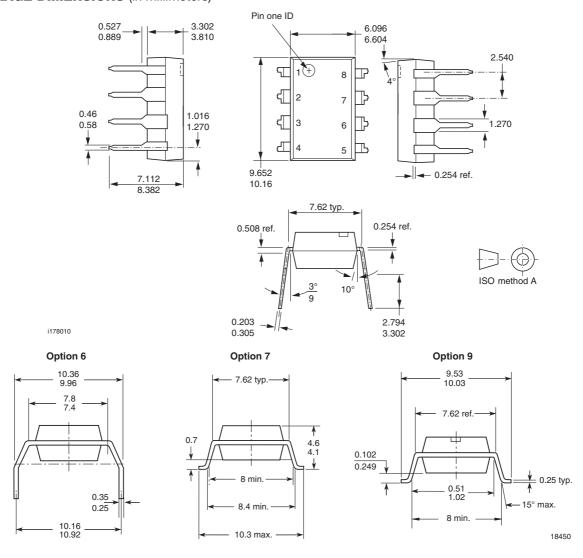
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These amplifiers provide either an inverting or non-inverting transfer gain based upon the type of input and output amplifier. Table 2 shows the various configurations along with the specific transfer gain equations. The offset column refers to the calculation of the output offset or V_{ref2} necessary to provide a zero voltage output for a zero voltage input. The non-inverting input amplifier requires the use of a bipolar supply, while the inverting input stage can be implemented with single supply operational amplifiers that permit operation close to ground.

For best results, place a buffer transistor between the LED and output of the operational amplifier when a CMOS opamp is used or the LED I_{Fq} drive is targeted to operate beyond 15 mA. Finally the bandwidth is influenced by the magnitude of the closed loop gain of the input and output amplifiers. Best bandwidths result when the amplifier gain is designed for unity.

PACKAGE DIMENSIONS (in millimeters)



PACKAGE MARKING (example of IL300-E-X001)

